# LVDS 4x4 CROSSPOINT SWITCH 

## FEATURES

- Greater Than 2.0 Gbps Operation
- Nonblocking Architecture Allows Each Output to be Connected to Any Input
- Pk-Pk Jitter:
- 60 ps Typical at 2.0 Gbps
- 110 ps Typical at 2.5 Gbps
- Compatible With ANSI TIA/EIA-644-A LVDS Standard
- Available Packaging 38-Pin TSSOP
- 25 mV of Input Voltage Threshold Hysteresis
- Propagation Delay Times: 800 ps Typical
- Inputs Electrically Compatible With LVPECL, CML and LVDS Signal Levels
- Operates From a Single 3.3-V Supply
- Low Power: 110 mA Typical
- Integrated 110- $\Omega$ Line Termination Resistors Available With SN65LVDT250


## APPLICATIONS

- Clock Buffering/Clock Muxing
- Wireless Base Stations
- High-Speed Network Routing
- Telecom/Datacom


## DESCRIPTION

The SN65LVDS250 and SN65LVDT250 are $4 \times 4$ nonblocking crosspoint switches in a flow-through pin-out allowing for ease in PCB layout. Low-voltage differential signaling (LVDS) is used to achieve a high-speed data throughput while using low power. Each of the output drivers includes a 4:1 multiplexer to allow any input to be routed to any output. Internal signal paths are fully differential to achieve the high signaling speeds while maintaining low signal skews. The SN65LVDT250 incorporates $110-\Omega$ termination resistors for those applications where board space is a premium.

The SN65LVDS250 and SN65LVDT250 are characterized for operation from $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$.

SN65LVDS250DBT ( Marked as LVDS250)
SN65LVDT250DBT ( Marked as LVDT250) (TOP VIEW)


EYE PATTERN

$V_{I C}=1.2 \mathrm{~V}$
$\left|V_{I D}\right|=200 \mathrm{mV}$
2 Gbps
Input $=$ PRBS $\mathbf{2 n}^{23} \mathbf{- 1}$
$\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## LOGIC DIAGRAM



Integrated Termination on LVDT Only

## EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

## INPUT LVDS250



Table 1. CROSSPOINT LOGIC TABLES

| OUTPUT CHANNEL 1 |  | OUTPUT CHANNEL 2 |  |  |  | OUTPUT CHANNEL 3 |  |  | OUTPUT CHANNEL 4 |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| CONTROL <br> PINS | INPUT <br> SELECTED | CONNTROL <br> PINS |  | INPUT <br> SELECTED | CONTROL <br> PINS | INPUT <br> SELECTED | CONTROL <br> PINS |  | INPUT <br> SELECTED |  |  |
| S10 | $\mathbf{S 1 1}$ | $\mathbf{1 Y} / \mathbf{1 Z}$ | $\mathbf{S 2 0}$ | $\mathbf{S 2 1}$ | $\mathbf{2 Y} / 2 Z$ | $\mathbf{S 3 0}$ | $\mathbf{S 3 1}$ | $\mathbf{3 Y} / \mathbf{3 Z}$ | $\mathbf{S 4 0}$ | $\mathbf{S 4 1}$ | $\mathbf{4 Y} / \mathbf{4 Z}$ |
| 0 | 0 | $1 \mathrm{~A} / 1 \mathrm{~B}$ | 0 | 0 | $1 \mathrm{~A} / 1 \mathrm{~B}$ | 0 | 0 | $1 \mathrm{~A} / 1 \mathrm{~B}$ | 0 | 0 | $1 \mathrm{~A} / 1 \mathrm{~B}$ |
| 0 | 1 | $2 \mathrm{~A} / 2 \mathrm{~B}$ | 0 | 1 | $2 \mathrm{~A} / 2 \mathrm{~B}$ | 0 | 1 | $2 \mathrm{~A} / 2 \mathrm{~B}$ | 0 | 1 | $2 \mathrm{~A} / 2 \mathrm{~B}$ |
| 1 | 0 | $3 \mathrm{~A} / 3 \mathrm{~B}$ | 1 | 0 | $3 \mathrm{~A} / 3 \mathrm{~B}$ | 1 | 0 | $3 \mathrm{~A} / 3 \mathrm{~B}$ | 1 | 0 | $3 \mathrm{~A} / 3 \mathrm{~B}$ |
| 1 | 1 | $4 \mathrm{~A} / 4 \mathrm{~B}$ | 1 | 1 | $4 \mathrm{~A} / 4 \mathrm{~B}$ | 1 | 1 | $4 \mathrm{~A} / 4 \mathrm{~B}$ | 1 | 1 | $4 \mathrm{~A} / 4 \mathrm{~B}$ |

## PACKAGE DISSIPATION RATINGS

| PACKAGE | CIRCUIT BOARD MODEL | $\mathrm{T}_{\mathrm{A}} \leq 25^{\circ} \mathrm{C}$ <br> POWER RATING | DERATING FACTOR ${ }^{(1)}$ ABOVE $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ <br> POWER RATING |
| :---: | :---: | :---: | :---: | :---: |
| TSSOP (DBT) | Low-K ${ }^{(2)}$ | 1038 mW | 9.0 mW/ ${ }^{\circ} \mathrm{C}$ | 496 mW |
| TSSOP (DBT) | High-K ${ }^{(3)}$ | 1772 mW | $15.4 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 847 mW |

(1) This is the inverse of the junction-to-ambient thermal resistance when board-mounded and with no air flow.
(2) In accordance with the Low-K thermal metric definitions of EIA/JESD51-6
(3) In accordance with the High-K thermal metric definitions of EIA/JESD51-6

## THERMAL CHARACTERISTICS

| PARAMETER | TEST CONDITIONS | VALUE | UNITS |
| :---: | :---: | :---: | :---: |
| $\Theta_{\mathrm{JB}} \quad$ Junction-to-board thermal resistance |  | 40.3 | $\mathrm{C} / \mathrm{W}$ |
| $\Theta_{\mathrm{JC}} \quad$ Junction-to-case thermal resistance |  | 8.5 |  |
| $\mathrm{P}_{\mathrm{D}}$ | Device power dissipation | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, 1 \mathrm{GHz}$ | 356 |
|  | $\mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=85^{\circ} \mathrm{C}, 1 \mathrm{GHz}$ | mW |  |

## ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted ${ }^{(1)}$

|  |  |  | UNITS |
| :---: | :---: | :---: | :---: |
| Supply voltage range, V |  |  | -0.5 V to 4 V |
|  | S, DE |  | -0.5 V to 4 V |
| Voltage range ${ }^{(2)}$ | A, B |  | -0.5 V to 4 V |
| Volage range | $\left\|\mathrm{V}_{\mathrm{A}}-\mathrm{V}_{\mathrm{B}}\right\|$ (LVDT only) |  | 1 V |
|  | Y, Z |  | -0.5 V to 4 V |
| Electrostatic discharge | Human body model ${ }^{(3)}$ | All pins | $\pm 3 \mathrm{kV}$ |
| E | Charged-device model ${ }^{(4)}$ | All pins | $\pm 500 \mathrm{~V}$ |
| Continuous power dissip |  |  | See Dissipation Rating Table |

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
(4) Tested in accordance with JEDEC Standard 22, Test Method C101.

## RECOMMENDED OPERATING CONDITIONS

|  |  |  | MIN | NOM | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Supply voltage |  | 3 | 3.3 | 3.6 | V |
| $\mathrm{V}_{\mathrm{IH}}$ | High-level input voltage | S10-S41, 1DE-4DE | 2 |  | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{V}_{\text {IL }}$ | Low-level input voltage | S10-S41, 1DE-4DE | 0 |  | 0.8 | V |
|  |  | LVDS | 0.1 |  | 1 | V |
| \| ID | ag | LVDT | 0.1 |  | 0.8 | V |
|  | Input voltage (any combination of com | de or input signals) | 0 |  | 3.3 | V |
| $\mathrm{T}_{\mathrm{J}}$ | Junction temperature |  |  |  | 140 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{A}}{ }^{(1)}$ | Operating free-air temperature |  | -40 |  | 85 | ${ }^{\circ} \mathrm{C}$ |

(1) Maximum free-air temperature operation is allowed as long as the device maximum junction temperature is not exceeded.

## TIMING SPECIFICATIONS

| PARAMETER |  |  | MIN NOM | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {SET }}$ | Input to select setup time | See Eigure 7 | 0.6 |  | ns |
| $\mathrm{t}_{\text {HOLD }}$ | Input to select hold time |  | 0.2 |  | ns |
| $\mathrm{t}_{\text {SWITCH }}$ | Select to switch output |  | 1.2 | 1.6 | ns |

## INPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted ${ }^{(1)}$

| PARAMETER |  |  | TEST CONDITIONS | MIN | TYP ${ }^{(1)}$ | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{1 \mathrm{~T}_{+}}$ | Positive-going differential input voltage threshold |  | See Eigure-1 |  |  | 100 | mV |
| $\mathrm{V}_{\text {IT }}$. | Negative-going differential input voltage threshold |  | See Eigure - | -100 |  |  | mV |
| $\mathrm{V}_{\text {ID(HYS }}$ | Differential input voltage hysteresis |  |  |  | 25 |  | mV |
| ${ }^{1} \mathrm{H}$ | High-level input current | 1DE-4DE | $\mathrm{V}_{1 \mathrm{H}}=2 \mathrm{~V}$ | -10 |  |  | $\mu \mathrm{A}$ |
|  |  | S10-S41 |  |  |  | 20 |  |
| IIL | Low-level input current | 1DE-4DE | $\mathrm{V}_{\mathrm{IL}}=0.8 \mathrm{~V}$ | -10 |  |  | $\mu \mathrm{A}$ |
|  |  | S10-S41 |  |  |  | 20 |  |
| 1 | Input current (A or B inputs) |  | $\mathrm{V}_{1}=0 \mathrm{~V}$ or 3.3 V , second input at 1.2 V (other input open for LVDT) | -20 |  | 20 | $\mu \mathrm{A}$ |
| $I_{\text {(OFF) }}$ | Input current (A or B inputs) |  | $\mathrm{V}_{\mathrm{CC}} \leq 1.5 \mathrm{~V}, \mathrm{~V}_{1}=0 \mathrm{~V}$ or 3.3 V , second input at 1.2 V (other input open for LVDT) | -20 |  | 20 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{10}$ |  |  | $\mathrm{V}_{\mathrm{IA}}=\mathrm{V}_{\text {IB }}, 0 \leq \mathrm{V}_{\text {IA }} \leq 3.3 \mathrm{~V}$ | -6 |  | 6 | $\mu \mathrm{A}$ |
| $\mathrm{R}_{\mathrm{T}}$ | Termination resistance (LVDT) |  | $\mathrm{V}_{\text {ID }}=300 \mathrm{mV}, \mathrm{V}_{\text {IC }}=0 \mathrm{~V}$ to 3.3 V | 90 | 110 | 132 | $\Omega$ |
|  | Termination resistance (LVDT with power-off) |  | $\begin{aligned} & \mathrm{V}_{\mathrm{ID}}=300 \mathrm{mV}, \mathrm{~V}_{\mathrm{IC}}=0 \mathrm{~V} \text { to } 3.3 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{CC}}=1.5 \mathrm{~V} \end{aligned}$ | 90 | 110 | 132 |  |
| $\mathrm{C}_{1}$ | Differential input capacitance |  |  |  | 2.5 |  | pF |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a 3.3 V supply.

## SLLS594B-MARCH 2004-REVISED OCTOBER 2004

## OUTPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

|  | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| \| $\mathrm{V}_{\text {OD }} \mid$ | Differential output voltage magnitude | $\begin{aligned} & \text { See Fiqure 2 } \\ & \mathrm{V}_{\mathrm{ID}}= \pm 100 \mathrm{mV} \end{aligned}$ | 247 | 350 | 454 | mV |
| $\Delta \mathrm{V}_{\text {OD }} \mid$ | Change in differential output voltage magnitude between logic states |  | -50 |  | 50 | mV |
| $\mathrm{V}_{\mathrm{OC}(\mathrm{SS})}$ | Steady-state common-mode output voltage | See Eigure3 | 1.125 |  | 1.375 | V |
| $\Delta \mathrm{V}_{\text {OC(SS }}$ | Change in steady-state common-mode output voltage between logic states |  | -50 |  | 50 | mV |
| $\mathrm{V}_{\mathrm{OC} \text { (PP) }}$ | Peak-to-peak common-mode output voltage |  |  | 50 | 150 | mV |
| $\mathrm{I}_{\mathrm{CC}}$ | Supply current | $\mathrm{R}_{\mathrm{L}}=100 \Omega$ |  | 110 | 145 | mA |
| $\mathrm{l}_{\mathrm{OS}}$ | Short-circuit output current | $\mathrm{V}_{\mathrm{OY}}$ or $\mathrm{V}_{\mathrm{OZ}}=0 \mathrm{~V}$ | -27 |  | 27 | mA |
| IOSD | Differential short circuit output current | $\mathrm{V}_{\mathrm{OD}}=0 \mathrm{~V}$ | -12 |  | 12 | mA |
| $\mathrm{l}_{\mathrm{Oz}}$ | High-impedance output current | $\mathrm{V}_{\mathrm{O}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ |  |  | $\pm 1$ | $\mu \mathrm{A}$ |
| $\mathrm{C}_{0}$ | Differential output capacitance |  |  | 2 |  | pF |

## SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

|  | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| tpLH | Propagation delay time, low-to-high-level output | See Eigure 4 | 700 | 800 | 1200 | ps |
| $\mathrm{t}_{\text {PHL }}$ | Propagation delay time, high-to-low-level output |  | 700 | 800 | 1200 |  |
| $\mathrm{t}_{\mathrm{r}}$ | Differential output signal rise time ( $20 \%-80 \%$ ) |  |  | 200 | 245 |  |
| $\mathrm{t}_{\mathrm{f}}$ | Differential output signal fall time (20\%-80\%) |  |  | 200 | 245 |  |
| $\mathrm{t}_{\text {sk(p) }}$ | Pulse skew (\| $\left.\mathrm{tPHL}^{-\mathrm{t}_{\text {PLLH }}}\right)^{(1)}$ |  |  | 0 | 50 | ps |
| $\mathrm{t}_{\text {sk(0) }}$ | Channel-to-channel output skew ${ }^{(2)}$ |  |  |  | 175 | ps |
| $\mathrm{t}_{\text {sk(pp) }}$ | Part-to-part skew ${ }^{(3)}$ |  |  |  | 300 | ps |
| $\mathrm{t}_{\text {jit }}$ (per) | Period jitter, rms (1 standard deviation) ${ }^{(4)}$ | See Eigure 6 |  | 1 | 3 | ps |
| $\mathrm{t}_{\mathrm{jit} \text { (cc) }}$ | Cycle-to-cycle jitter (peak) ${ }^{(5)}$ | See Figure6 |  | 8 | 17 | ps |
| $\mathrm{t}_{\mathrm{jit} \text { (pp) }}$ | Peak-to-peak jitteR ${ }^{(6)}$ | See Figure 6 |  | 60 | 110 | ps |
| $\mathrm{t}_{\mathrm{jit} \text { (det) }}$ | Deterministic jitter, peak-to-peak ${ }^{(7)}$ | See Figure 6 |  | 48 | 65 | ps |
| $\mathrm{t}_{\text {PHZ }}$ | Propagation delay, high-level-to-high-impedance output | See Eigure.5 |  |  | 6 | ns |
| tpLZ | Propagation delay, low-level-to-high-impedance output |  |  |  | 6 |  |
| $t_{\text {pzH }}$ | Propagation delay, high-impedance -to-high-level output |  |  |  | 300 |  |
| $\mathrm{t}_{\text {PZL }}$ | Propagation delay, high-impedance-to-low-level output |  |  |  | 300 |  |

(1) $t_{\text {sk(p) })}$ is the magnitude of the time difference between the $t_{P L H}$ and $t_{P H L}$ of any output of a single device.
(2) $\mathrm{t}_{\mathrm{sk}(0)}$ is the maximum delay time difference between drivers over temperature, $\mathrm{V}_{\mathrm{CC}}$, and process.
(3) $t_{\text {sk }(p p)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.
(4) Input voltage $=V_{I D}=200 \mathrm{mV}, 50 \%$ duty cycle at $1.0 \mathrm{GHz}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}$ ( $20 \%$ to $80 \%$ ), measured over 1000 samples.
(5) Input voltage $=V_{I D}=200 \mathrm{mV}, 50 \%$ duty cycle at $1.0 \mathrm{GHz}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$.
(6) Input voltage $=V_{I D}=200 \mathrm{mV}, 2^{23}-1$ PRBS pattern at $2.0 \mathrm{Gbps}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}$ ( $20 \%$ to $80 \%$ ), measured over 200k samples.
(7) Input voltage $=V_{I D}=200 \mathrm{mV}, 2^{7-1}$ PRBS pattern at $2.0 \mathrm{Gbps}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$.

## PARAMETER MEASUREMENT INFORMATION



Figure 1. Voltage and Current Definitions


Figure 2. Differential Output Voltage ( $\mathrm{V}_{\mathrm{OD}}$ ) Test Circuit

A. All input pulses are supplied by a generator having the following characteristics: $\mathrm{t}_{\mathrm{r}}$ or $\mathrm{t}_{\mathrm{f}} \leq 1 \mathrm{~ns}$, pulse-repetition rate (PRR) $=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} ; \mathrm{R}_{\mathrm{L}}=100 \Omega ; \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the DUT; the measurement of $\mathrm{V}_{\mathrm{OC}(\mathrm{PP})}$ is made on test equipment with a -3 dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions fot the Driver Common-Mode Output Voltage

A. All input pulses are supplied by a generator having the following characteristics: $\mathrm{t}_{\mathrm{r}}$ or $\mathrm{t}_{\mathrm{f}} \leq 0.25 \mathrm{~ns}$, pulse-repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} . \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the DUT.

Figure 4. Timing Test Circuit and Waveforms

PARAMETER MEASUREMENT INFORMATION (continued)


A. All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq 1 \mathrm{~ns}$, pulse-repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} . \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the DUT.

Figure 5. Enable and Disable Time Circuit and Definitions

A. All input pulses are supplied by an Agilent 81250 Stimulus System.
B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software.

Figure 6. Driver Jitter Measurement Waveforms

## PARAMETER MEASUREMENT INFORMATION (continued)



DE



DE
A. $\quad t_{S E T}$ and $t_{\text {HOLD }}$ times specify that data must be in a stable state before and after mux control switches.

Figure 7. Input to Select for Both Rising and Falling Edge Setup and Hold Times

## TYPICAL CHARACTERISTICS



Figure 8.

PEAK-TO-PEAK JITTER
vs FREQUENCY


Figure 11.


Figure 14.

PROPAGATION DELAY TIME
FREE-AIR TEMPERATURE


Figure 9.

PEAK-TO-PEAK JITTER
vs
DATA RATE


Figure 12.
PEAK-TO-PEAK JITTER
vs
FREQUENCY


Figure 15.

PROPAGATION DELAY TIME COMMON-MODE INPUT VOLTAGE


Figure 10.

PEAK-TO-PEAK JITTER
vs
FREQUENCY


Figure 13.
PEAK-TO-PEAK JITTER
VS
DATA RATE


Figure 16.

## TYPICAL CHARACTERISTICS (continued)



Figure 17.
DIFFERENTIAL OUTPUT VOLTAGE FREQUENCY


Figure 19.


Figure 18.


60 - ps/div
$\mathrm{V}_{\text {IC }}=1.2 \mathrm{~V},\left|\mathrm{~V}_{\mathrm{ID}}\right|=200 \mathrm{mV}, 2.5 \mathrm{Gbps}$, Input $=$ PRBS $\mathbf{2 T}^{23} \mathbf{- 1}, \mathrm{~V}_{\mathrm{CC}}=3.3 \mathrm{~V}$

Figure 20.

## APPLICATION INFORMATION

## CONFIGURATION EXAMPLES

| S10 | S11 | S20 | S21 |
| :---: | :---: | :---: | :---: |
| 0 | 0 | 0 | 1 |
| S30 | S31 | S40 | S41 |
| 1 | 0 | 1 | 1 |



| S10 | S11 | S20 | S21 |
| :---: | :---: | :---: | :---: |
| 0 | 0 | 0 | 0 |
| S30 | S31 | S40 | S41 |
| 1 | 0 | 1 | 0 |



| S10 | S11 | S20 | S21 |
| :---: | :---: | :---: | :---: |
| 0 | 0 | 0 | 0 |
| S30 | S31 | S40 | S41 |
| 0 | 0 | 0 | 0 |



| S10 | S11 | S20 | S21 |
| :---: | :---: | :---: | :---: |
| 1 | 1 | 1 | 1 |
| S30 | S 31 | S 40 | S 41 |
| 0 | 0 | 0 | 0 |



APPLICATION INFORMATION (continued)
TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)


Figure 21. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)


Figure 22. Current-Mode Logic (CML)


Figure 23. Single-Ended (LVPECL)


Figure 24. Low-Voltage Differential Signaling (LVDS)

## PACKAGING INFORMATION

| Orderable Device | Status <br> (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan <br> (2) | Lead/Ball Finish <br> (6) | MSL Peak Temp <br> (3) | Op Temp ( ${ }^{\circ} \mathrm{C}$ ) | Device Marking <br> (4/5) | Samples |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVDS250DBT | ACTIVE | TSSOP | DBT | 38 | 50 | $\begin{gathered} \text { Green (RoHS } \\ \& \text { no } \mathrm{Sb} / \mathrm{Br} \text { ) } \\ \hline \end{gathered}$ | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | LVDS250 | Samples |
| SN65LVDS250DBTR | ACTIVE | TSSOP | DBT | 38 | 2000 | Green (RoHS $\&$ no $\mathrm{Sb} / \mathrm{Br}$ ) | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | LVDS250 | Samples |
| SN65LVDS250DBTRG4 | ACTIVE | TSSOP | DBT | 38 | 2000 | Green (RoHS $\&$ no $\mathrm{Sb} / \mathrm{Br})$ | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | LVDS250 | Samples |
| SN65LVDT250DBT | ACTIVE | TSSOP | DBT | 38 | 50 | $\begin{gathered} \text { Green (RoHS } \\ \& \text { no } \mathrm{Sb} / \mathrm{Br} \text { ) } \\ \hline \end{gathered}$ | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | LVDT250 | Samples |
| SN65LVDT250DBTR | ACTIVE | TSSOP | DBT | 38 | 2000 | $\begin{gathered} \text { Green (RoHS } \\ \& \text { no } \mathrm{Sb} / \mathrm{Br}) \end{gathered}$ | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | LVDT250 | Samples |

${ }^{(1)}$ The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.
${ }^{(2)}$ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed $0.1 \%$ by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of $<=1000$ ppm threshold. Antimony trioxide based flame retardants must also meet the $<=1000$ ppm threshold requirement.
${ }^{(3)}$ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
${ }^{(4)}$ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
${ }^{(5)}$ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a " $\sim$ " will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
${ }^{(6)}$ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter $(\mathrm{mm})$ | Reel <br> Width <br> W1 (mm) | $\begin{gathered} \mathrm{AO} \\ (\mathrm{~mm}) \end{gathered}$ | $\begin{gathered} \mathrm{BO} \\ (\mathrm{~mm}) \end{gathered}$ | $\begin{gathered} \text { K0 } \\ (\mathrm{mm}) \end{gathered}$ | $\begin{gathered} \text { P1 } \\ (\mathrm{mm}) \end{gathered}$ | $\begin{gathered} \mathrm{W} \\ (\mathrm{~mm}) \end{gathered}$ | Pin1 <br> Quadrant |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVDS250DBTR | TSSOP | DBT | 38 | 2000 | 330.0 | 16.4 | 6.9 | 10.2 | 1.8 | 12.0 | 16.0 | Q1 |
| SN65LVDT250DBTR | TSSOP | DBT | 38 | 2000 | 330.0 | 16.4 | 6.9 | 10.2 | 1.8 | 12.0 | 16.0 | Q1 |


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVDS250DBTR | TSSOP | DBT | 38 | 2000 | 350.0 | 350.0 | 43.0 |
| SN65LVDT250DBTR | TSSOP | DBT | 38 | 2000 | 350.0 | 350.0 | 43.0 |

## PACKAGE OUTLINE



## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

NOTES: (continued)
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.


SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL SCALE: 10X

NOTES: (continued)
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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